## DISCRETE SEMICONDUCTORS

## DATA SHEET

# **BFT93**PNP 5 GHz wideband transistor

**Product specification** 

November 1992



## **PNP 5 GHz wideband transistor**

**BFT93** 

#### **DESCRIPTION**

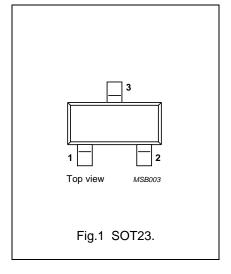
PNP transistor in a plastic SOT23 envelope.

It is primarily intended for use in RF wideband amplifiers, such as in aerial amplifiers, radar systems, oscilloscopes, spectrum analyzers, etc. The transistor features low intermodulation distortion and high power gain; due to its very high transition frequency, it also has excellent wideband properties and low noise up to high frequencies.

NPN complements are BFR93 and BFR93A.

#### **PINNING**

| PIN | DESCRIPTION |  |  |
|-----|-------------|--|--|
|     | Code: X1p   |  |  |
| 1   | base        |  |  |
| 2   | emitter     |  |  |
| 3   | collector   |  |  |



## **QUICK REFERENCE DATA**

| SYMBOL           | PARAMETER                     | CONDITIONS  | TYP. | MAX. | UNIT |
|------------------|-------------------------------|---|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter  | _    | -15  | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base   | _    | -12  | V    |
| I <sub>c</sub>   | DC collector current          |   | _    | -35  | mA   |
| P <sub>tot</sub> | total power dissipation       | up to T <sub>s</sub> = 95 °C; note 1  | _    | 300  | mW   |
| f <sub>T</sub>   | transition frequency          | $I_C = -30 \text{ mA}; V_{CE} = -5 \text{ V}; f = 500 \text{ MHz};$<br>$T_j = 25 ^{\circ}\text{C}$  | 5    | -    | GHz  |
| C <sub>re</sub>  | feedback capacitance          | $I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}; f = 1 \text{ MHz}$   | 1    | _    | pF   |
| G <sub>UM</sub>  | maximum unilateral power gain | $I_C = -30 \text{ mA}; V_{CE} = -5 \text{ V}; f = 500 \text{ MHz};$<br>$T_{amb} = 25 \text{ °C}$  | 16.5 | _    | dB   |
| F                | noise figure                  | $I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}; f = 500 \text{ MHz};$<br>$T_{amb} = 25 \text{ °C}$  | 2.4  | _    | dB   |
| Vo               | output voltage                | $\begin{aligned} & d_{im} = -60 \text{ dB; } I_C = -30 \text{ mA;} \\ & V_{CE} = -5 \text{ V; } R_L = 75 \Omega; \\ & f_{(p+q-r)} = 493.25 \text{ MHz} \end{aligned}$ | 300  | -    | mV   |

## Note

1.  $T_s$  is the temperature at the soldering point of the collector tab.

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## **LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 134).

| SYMBOL           | PARAMETER                 | CONDITIONS                           | MIN. | MAX. | UNIT |
|------------------|---------------------------|--------------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                         | _    | -15  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                            | _    | -12  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                       | _    | -2   | V    |
| I <sub>C</sub>   | DC collector current      |                                      | _    | -35  | mA   |
| I <sub>CM</sub>  | peak collector current    | f > 1 MHz                            | _    | -50  | mA   |
| P <sub>tot</sub> | total power dissipation   | up to T <sub>s</sub> = 95 °C; note 1 | _    | 300  | mW   |
| T <sub>stg</sub> | storage temperature       |                                      | -65  | 150  | °C   |
| Tj               | junction temperature      |                                      | _    | 175  | °C   |

## THERMAL RESISTANCE

| SYMBOL              | PARAMETER   | CONDITIONS                                   | THERMAL RESISTANCE |  |
|---------------------|---|--|--------------------|--|
| R <sub>th j-s</sub> | thermal resistance from junction to soldering point | up to $T_s = 70 ^{\circ}\text{C}$ ; (note 1) | 260 K/W            |  |

## Note

1.  $T_{\mbox{\scriptsize S}}$  is the temperature at the soldering point of the collector tab.

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## **CHARACTERISTICS**

T<sub>i</sub> = 25 °C unless otherwise specified.

| SYMBOL           | PARAMETER                              | CONDITIONS   | MIN. | TYP. | MAX. | UNIT |
|------------------|--|--|------|------|------|------|
| I <sub>CBO</sub> | collector cut-off current              | $I_E = 0; V_{CB} = -5 \text{ V}$   | _    | _    | -50  | nA   |
| h <sub>FE</sub>  | DC current gain                        | $I_C = -30 \text{ mA}; V_{CE} = -5 \text{ V}$  | 20   | 50   | _    |      |
| f <sub>T</sub>   | transition frequency                   | $I_C = -30 \text{ mA}; V_{CE} = -5 \text{ V};$<br>f = 500 MHz                            | _    | 5    | _    | GHz  |
| C <sub>c</sub>   | collector capacitance                  | $I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$                         | _    | 0.95 | _    | pF   |
| C <sub>e</sub>   | emitter capacitance                    | $I_c = I_c = 0$ ; $V_{EB} = -0.5 \text{ V}$ ; $f = 1 \text{ MHz}$                        | _    | 1.8  | _    | pF   |
| C <sub>re</sub>  | feedback capacitance                   | $I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}; f = 1 \text{ MHz}$                          | _    | 1    | _    | pF   |
| G <sub>UM</sub>  | maximum unilateral power gain (note 1) | $I_C = -30 \text{ mA}; V_{CE} = -5 \text{ V};$<br>f = 500 MHz; $T_{amb} = 25 \text{ °C}$ | _    | 16.5 | _    | dB   |
| F                | noise figure                           | $I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V};$<br>f = 500 MHz; $T_{amb} = 25 \text{ °C}$ | _    | 2.4  | -    | dB   |
| Vo               | output voltage                         | see Fig.2 and note 2   | _    | 300  | _    | mV   |

#### **Notes**

1.  $G_{UM}$  is the maximum unilateral power gain, assuming  $S_{12}$  is zero and

$$G_{UM} = 10 \log \frac{\left|S_{21}\right|^2}{(1 - \left|S_{11}\right|^2)(1 - \left|S_{22}\right|^2)} dB.$$

2.  $d_{im}$  = -60 dB (DIN 45004B);  $I_C$  = -30 mA;  $V_{CE}$  = -5 V;  $R_L$  = 75  $\Omega$ ;

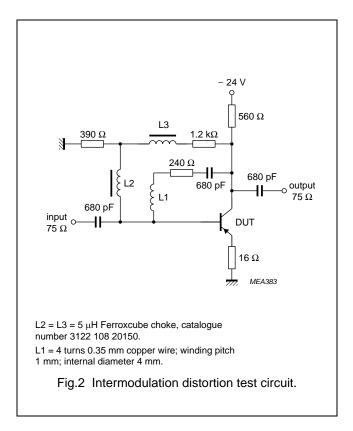
 $V_p = V_o$  at  $d_{im} = -60$  dB;  $f_p = 495.25$  MHz;  $V_q = V_o - 6$  dB;  $f_q = 503.25$  MHz;

 $V_r = V_o -6 \text{ dB}; f_r = 505.25 \text{ MHz};$ 

measured at  $f_{(p+q-r)} = 493.25$  MHz.

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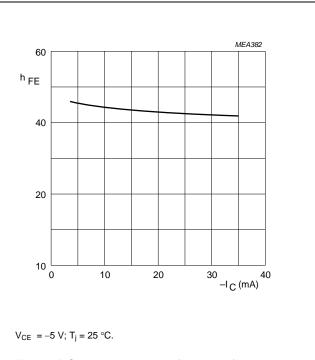
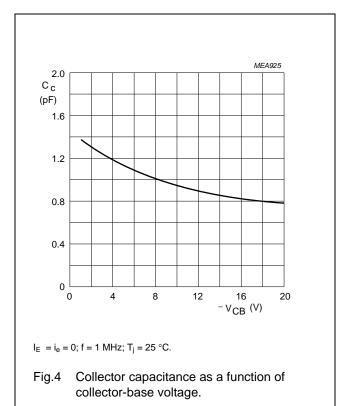
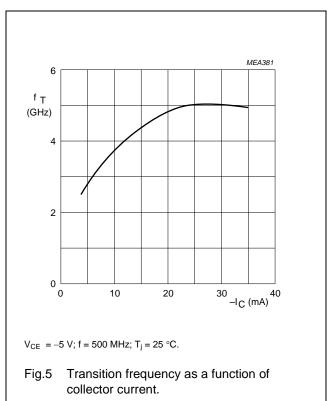


Fig.3 DC current gain as a function of collector current.





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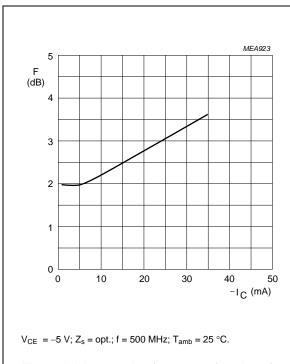


Fig.6 Minimum noise figure as a function of collector current.

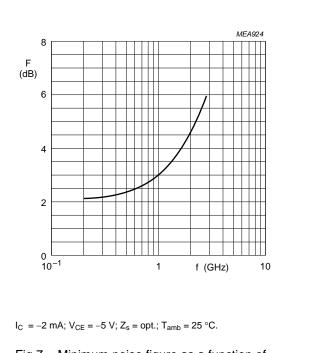


Fig.7 Minimum noise figure as a function of frequency.

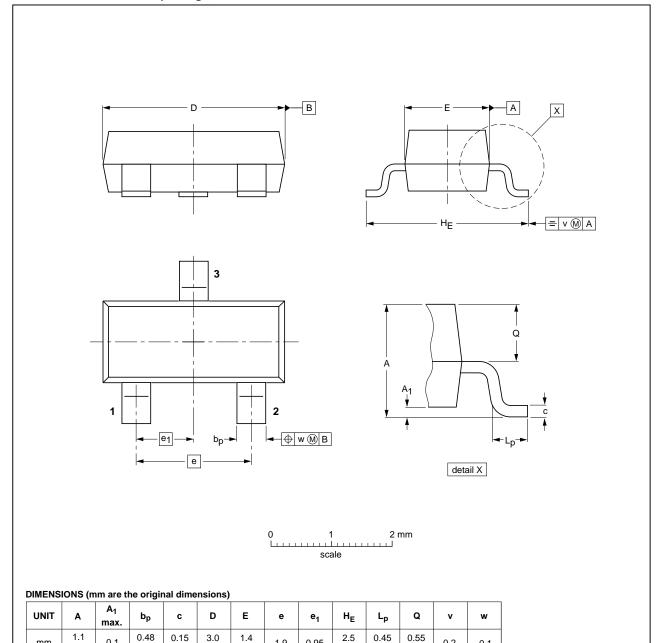
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## **PACKAGE OUTLINE**

Plastic surface-mounted package; 3 leads

SOT23



| OUTLINE | REFERENCES |          |       | EUROPEAN | ISSUE DATE |                                  |
|---------|------------|----------|-------|----------|------------|----------------------------------|
| VERSION | IEC        | JEDEC    | JEITA |          | PROJECTION | ISSUE DATE                       |
| SOT23   |            | TO-236AB |       |          |            | <del>-04-11-04</del><br>06-03-16 |

0.2

0.1

0.95

1.9

mm

0.1

0.9

0.38

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|-----------------------------------|----------------------------------|---|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
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